

Silicon NPN Power Transistors

2SC4764

DESCRIPTION

- With TO-3P(H)IS package
- High speed
- High voltage
- Low saturation voltage
- Built-in damper diode

Silicon NPN Power Transistors

2SC4764

CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =300mA ; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A ; I _B =0.8A			5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4A ; I _B =0.8A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =1500V ; I _E =0			1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V ; I _C =0	83		250	mA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	8	12		
h _{FE-2}	DC current gain	I _C =4A ; V _{CE} =5V	5		9	
C _{ob}	Collector output capacitance	I _E =0 ; V _{CB} =10V, f=1MHz		170		pF
V _F	Diode forward voltage	I _F =4A		1.2	1.8	V
f _T	Transition frequency	I _C =0.1A ; V _{CE} =10V	1	3		MHz

Switching times resistive load

t _s	Storage time	I _{CP} =4A ; I _{B1} =0.8A I _{B2} =-1.6A ; R _L =51		1.6	2.5	μs
t _f	Fall time			0.1	0.2	μs

Silicon NPN Power Transistors

2SC4764

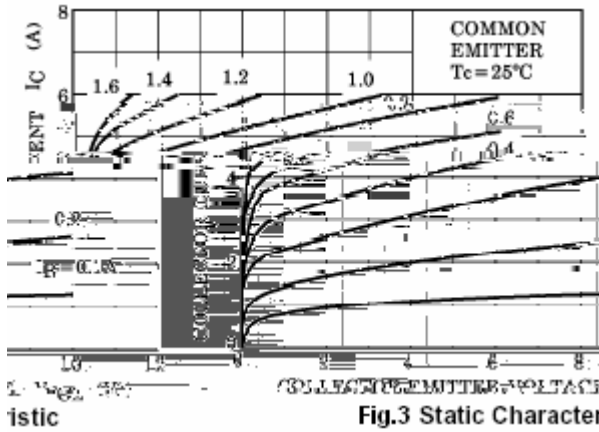


Fig.3 Static Characteristic

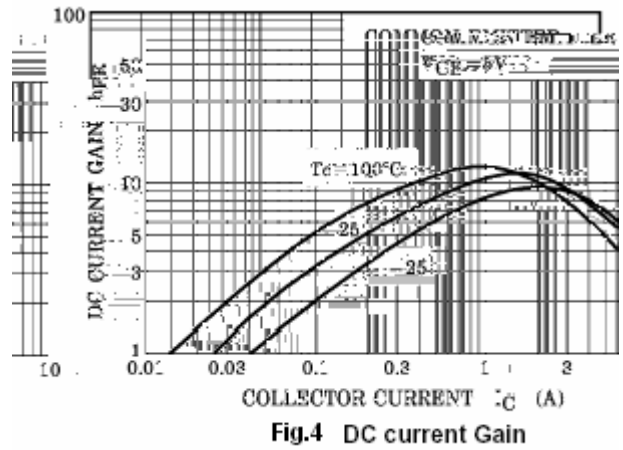


Fig.4 DC current Gain

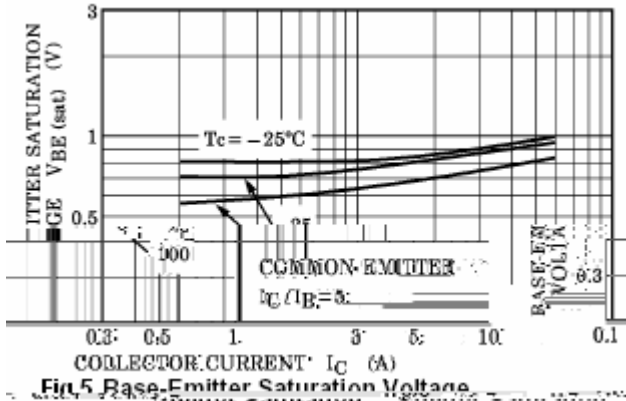


Fig.5 Base-Emitter Saturation Voltage

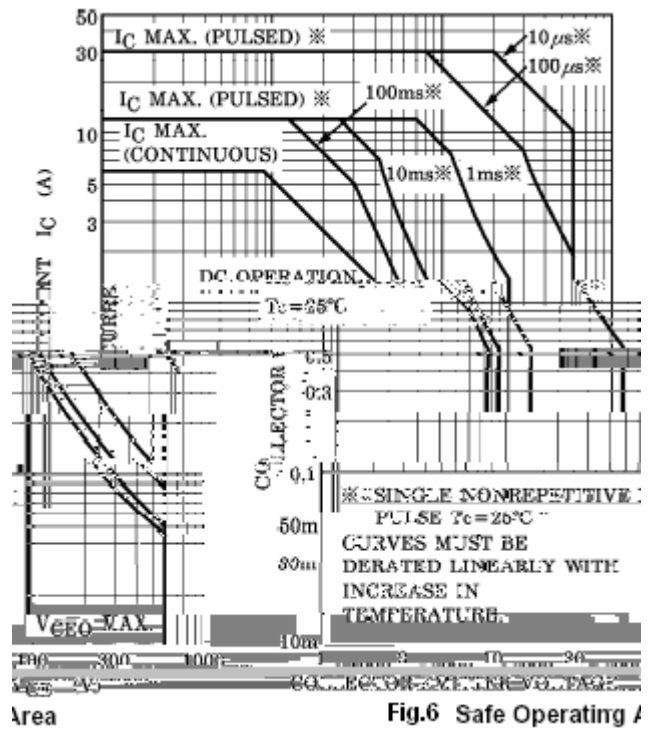


Fig.6 Safe Operating Area